

2022 IEEE Workshop on Wide Bandgap Power Devices and Applications in Europe (WiPDA Europe 2022)

**Coventry, United Kingdom
18 – 20 September 2022**



**IEEE Catalog Number: CFP22CO8-POD
ISBN: 978-1-6654-8815-0**

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IEEE Catalog Number:	CFP22CO8-POD
ISBN (Print-On-Demand):	978-1-6654-8815-0
ISBN (Online):	978-1-6654-8814-3

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2022 IEEE Workshop on Wide Bandgap Power Devices and Applications in Europe (WiPDA Europe)

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